

**T1310DFB/R1550nm 155M LC BOSA**

**FB-A5253ASL-00**

**Features:**

High stability DFB laser chip  
InGaAs/InP PIN detector with TIA  
Operate temperature from -40°C to +85°C  
LC Receptacle

**Specification:**

**Absolute Maximum Ratings**

Parameter	Symbol	Condition	Min	Max	Unit
Operating Case Temperature	$T_c$	--	-40	85	°C
Storage Temperature	$T_{stg}$	--	-40	85	°C
Lead solder Temperature	--	--		260	°C
Lead Soldering Time	--	--		10	s

**Optical/Electrical Characteristics (T=25°C, unless otherwise stated)**

**1310nm FP Laser Transmitter**

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Optical Output Power	$P_o$	2.0	--	4.0	mW	CW, $I_{op}=30mA$
Threshold Current	$I_{th}$	--	8	15	mA	T=25 °C
Forward Voltage	$V_F$	--	1.1	1.6	V	
Operating Current	$I_{op}$	--	30	35	mA	CW, T=25 °C
Center Wavelength	$\lambda_c$	1290	1310	1330	nm	CW, T=25 °C
Spectral Width (-20 dB)	$\Delta\lambda$	--	0.1	1.0	nm	
Wavelength temperature coefficient	$\Delta\lambda/\Delta T$		0.08	0.12	nm/°C	
Side-Mode Suppression Ratio	SMSR	30	40		dB	$I_{op}=30mA$
Relaxation Oscillation Frequency	$f_R$	--	4.5	--	GHZ	$I_{op}=30mA$
Rise/Fall Times	$t_R, t_F$	--	--	0.1	ns	20% to 80%
Monitor Current	$I_{mon}$	100	--	1000	μA	$V_R=5 V,$
Monitor Dark Current	$I_D$	--	--	200	nA	$V_R=5 V$

**1550nm 155Mbps Receiver**

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Supply Voltage	VCC	3.0	-	5.5	V	
Supply Current	ICC	-	-	35	mA	No loads
Differential responsivity	$R_d$	0.1	--	120	mV/uW	$R_{load}=100 \Omega, \lambda=1550nm$
Single ended responsivity	$R_s$	0.05	--	60	mV/uW	$R_{load}=50 \Omega, \lambda=1550nm$
Small-Signal Bandwidth	Bw	115	-	-	MHZ	$\lambda = 1550 nm, P_f=10uW$
Rise /Fall Time(20%~80%)	$Tr/f$		-	4.5	ns	$\lambda = 1550 nm, P_f=10uW$
Saturation Power	$P_{sat}$	-3			dBm	$\lambda=1550nm$
Wavelength	$\lambda$	1450	1550	1600	nm	

**江苏飞格光电有限公司**  
**JIANGSU FIBER GRID CO., LTD**

Single ended output impedance	Ro	--	50	--	ohm	
Sensitivity			-36	-34	dBm	$\lambda = 1550 \text{ nm}$ , 155Mbps, BER=1E-10

**Dimensions And Package Outline**

